

Day : Monday  
Date: 11/14/2005


**PALM INTRANET**

Time: 13:58:14

**Inventor Name Search Result**

Your Search was:

Last Name = BENSACHEL

First Name = DANIEL

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>06042081</u>	<u>4263056</u>	150	05/24/1979	METHOD FOR THE MANUFACTURE OF LIGHT EMITTING AND/OR PHOTODETECTIVE DIODES	BENSACHEL, DANIEL
<u>06085948</u>	<u>4229237</u>	150	10/18/1979	METHOD OF FABRICATION OF SEMICONDUCTOR COMPONENTS HAVING OPTOELECTRONIC CONVERSION PROPERTIES	BENSACHEL, DANIEL
<u>06853906</u>	<u>4678538</u>	250	04/21/1986	PROCESS FOR THE PRODUCTION OF AN INSULATING SUPPORT ON AN ORIENTED MONOCRYSTALLINE SILICON FILM WITH LOCALIZED DEFECTS	BENSACHEL, DANIEL
<u>06882901</u>	<u>4725561</u>	150	06/05/1986	PROCESS FOR THE PRODUCTION OF MUTUALLY ELECTRICALLY INSULATED MONOCRYSTALLINE SILICON ISLANDS USING LASER RECRYSTALLIZATION	BENSACHEL, DANIEL
<u>07808745</u>	<u>5252181</u>	150	12/17/1991	METHOD FOR CLEANING THE SURFACE OF A SUBSTRATE WITH PLASMA	BENSACHEL, DANIEL
<u>07914380</u>	Not Issued	161	07/15/1992	DEVICE FOR INJECTING A PRODUCT INTO AN ENCLOSED CHAMBER SUCH AS A REACTOR FOR MICROELECTRONICS	BENSACHEL, DANIEL
<u>08797511</u>	<u>5876796</u>	150	12/23/1996	PROCESS FOR SELECTIVELY DEPOSITING A REFRACTORY METAL SILICIDE ON SILICON, AND SILICON WAFER	BENSACHEL, DANIEL

				METALLIZED USING THIS PROCESS	
<u>09217025</u>	<u>6117750</u>	150	12/21/1998	PROCESS FOR OBTAINING A LAYER OF SINGLE-CRYSTAL GERMANIUM OR SILICON ON A SUBSTRATE OF SINGLE-CRYSTAL SILICON OR GERMANIUM, RESPECTIVELY	BENSAHEL, DANIEL
<u>09403356</u>	<u>6372581</u>	150	10/18/1999	PROCESS FOR NITRIDING THE GATE OXIDE LAYER OF A SEMICONDUCTOR DEVICE AND DEVICE OBTAINED	BENSAHEL, DANIEL
<u>09403442</u>	<u>6255149</u>	150	10/19/1999	PROCESS FOR RESTRICTING INTERDIFFUSION IN A SEMICONDUCTOR DEVICE WITH COMPOSITE SI/SIGE GATE	BENSAHEL, DANIEL
<u>09540188</u>	<u>6399502</u>	150	03/31/2000	PROCESS FOR FABRICATING A PLANAR HETEROSTRUCTURE	BENSAHEL, DANIEL
<u>09659913</u>	<u>6429098</u>	150	09/11/2000	PROCESS FOR OBTAINING A LAYER OF SINGLE-CRYSTAL GERMANIUM OR SILICON ON A SUBSTRATE OF SINGLE-CRYSTAL SILICON OR GERMANIUM, RESPECTIVELY, AND MULTILAYER PRODUCTS OBTAINED	BENSAHEL, DANIEL
<u>09763532</u>	<u>6551698</u>	150	04/04/2001	METHOD FOR TREATING A SILICON SUBSTRATE, BY NITRIDING, TO FORM A THIN INSULATING LAYER	BENSAHEL, DANIEL
<u>09786996</u>	<u>6537370</u>	150	03/09/2001	PROCESS FOR OBTAINING A LAYER OF SINGLE-CRYSTAL GERMANIUM ON A SUBSTRATE OF SINGLE-CRYSTAL SILICON, AND PRODUCTS OBTAINED	BENSAHEL, DANIEL
<u>09921642</u>	<u>6596555</u>	150	08/03/2001	FORMING OF QUANTUM DOTS	BENSAHEL, DANIEL
<u>10048719</u>	<u>6690027</u>	150	06/13/2002	METHOD FOR MAKING A DEVICE COMPRISING LAYERS OF PLANES OF QUANTUM DOTS	BENSAHEL, DANIEL
<u>10405075</u>	Not	95	03/31/2003	STRAINED-CHANNEL	BENSAHEL,

	Issued			ISOLATED-GATE FIELD EFFECT TRANSISTOR, PROCESS FOR MAKING SAME AND RESULTING INTEGRATED CIRCUIT	DANIEL
<u>10614675</u>	Not Issued	71	07/07/2003	Growth of a single-crystal region of a III-V compound on a single-crystal silicon substrate	BENSAHEL, DANIEL
<u>10615259</u>	<u>6953736</u>	150	07/09/2003	PROCESS FOR TRANSFERRING A LAYER OF STRAINED SEMICONDUCTOR MATERIAL	BENSAHEL, DANIEL
<u>10744680</u>	<u>6969661</u>	150	12/23/2003	METHOD FOR FORMING A LOCALIZED REGION OF A MATERIAL DIFFICULT TO ETCH	BENSAHEL, DANIEL
<u>10815473</u>	Not Issued	30	04/01/2004	Method of fabricating a semiconductor device comprising a gate dielectric made of high dielectric permittivity material	BENSAHEL, DANIEL
<u>10816214</u>	Not Issued	30	04/01/2004	Heteroatomic single-crystal layers	BENSAHEL, DANIEL
<u>10882995</u>	Not Issued	30	07/01/2004	Process for fabricating strained layers of silicon or of a silicon/germanium alloy	BENSAHEL, DANIEL
<u>11165339</u>	Not Issued	30	06/24/2005	Process for transferring a layer of strained semiconductor material	BENSAHEL, DANIEL
<u>60445825</u>	Not Issued	159	02/10/2003	Process for transferring a layer of strained semiconductor material	BENSAHEL, DANIEL
<u>60461656</u>	Not Issued	159	04/09/2003	Terahertz sources and detectors based on silicon and silicon germanium alloys and method of manufacture	BENSAHEL, DANIEL

Inventor Search Completed: No Records to Display.

	<b>Last Name</b>	<b>First Name</b>	
<b>Search Another: Inventor</b>	<input type="text" value="Bensahel"/>	<input type="text" value="Daniel"/>	<input type="button" value="Search"/>

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